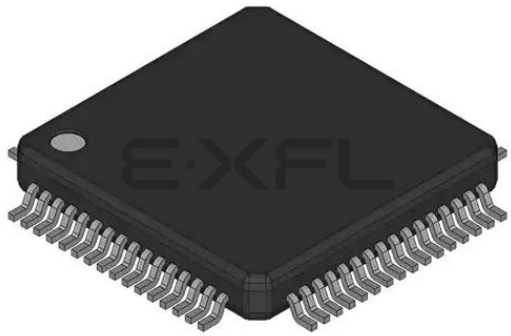

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	Coldfire V1
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I²C, SCI, SPI
Peripherals	DMA, LVD, PWM, WDT
Number of I/O	53
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 19x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-QFP
Supplier Device Package	64-QFP (14x14)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mcf51ag96vqh

- System Clock Sources
  - Oscillator (XOSC) — Loop-control pierce oscillator; crystal or ceramic resonator range of 31.25 kHz to 38.4 kHz or 1 MHz to 16 MHz
  - Internal Clock Source (ICS) — Frequency-locked-loop (FLL) controlled by internal or external reference; trimmable internal reference allows 0.2% resolution and 2% deviation (1% across 0 to 70 ºC)
- Peripherals
  - ADC — 24 analog inputs with 12 bits resolution; output formatted in 12-, 10- or 8-bit right-justified format; single or continuous conversion (automatic return to idle after single conversion); interrupt or DMA request when conversion complete; operation in low-power modes for lower noise operation; asynchronous clock source for lower noise operation; selectable asynchronous hardware conversion triggers from RTC, PDB, or iEvent; dual samples based on hardware triggers during ping-pong mode; on-chip temperature sensor
  - PDB — 16-bit of resolution with prescaler; seven possible trigger events input; positive transition of trigger event signal initiates the counter; support continuous trigger or single shot, bypass mode; supports two triggered delay outputs or ORed together; pulsed output could be used for HSCMP windowing signal
  - iEvent — User programmable combinational boolean output using the four selected iEvent input channels for use as interrupt requests, DMA transfer requests, or hardware triggers
  - FTM — Two 6-channel flexible timer/PWM modules with DMA request option; deadtime insertion is available for each complementary channel pair; channels operate as pairs with equal outputs, pairs with complimentary outputs or independent channels (with independent outputs); 16-bit free-running counter; the load of the FTM registers which have write buffer can be synchronized; write protection for critical registers; backwards compatible with TPM
  - TPM — 16-bit free-running or modulo up/down count operation; two channels, each channel may be input capture, output compare, or edge-aligned PWM; one interrupt per channel plus terminal count interrupt
  - CRC — High speed hardware CRC generator circuit using 16-bit shift register; CRC16-CCITT compliancy with $x^{16} + x^{12} + x^5 + 1$ polynomial; error detection for all single, double, odd, and most multi-bit errors; programmable initial seed value
  - HSCMP — Two analog comparators with selectable interrupt on rising edge, falling edge, or either edges of comparator output; the positive and negative inputs of the comparator are both driven from 4-to-1 muxes; programmable voltage reference from two internal DACs; support DMA transfer
  - IIC — Compatible with IIC bus standard and SMBus version 2 features; up to 100 kbps with maximum bus loading; multi-master operation; software programmable for one of 64 different serial clock frequencies; programmable slave address and glitch input filter; interrupt driven byte-by-byte data transfer; arbitration lost interrupt with automatic mode switching from master to slave; calling address identification interrupt; bus busy detection; broadcast and 10-bit address extension; address matching causes wake-up when MCU is in Stop3 mode; DMA support
  - SCI — Two serial communications interface modules with optional 13-bit break; full-duplex, standard non-return-to-zero (NRZ) format; double-buffered transmitter and receiver with separate enables; 13-bit baud rate selection with /32 fractional divide; interrupt-driven or polled operation; hardware parity generation and checking; programmable 8-bit or 9-bit character length; receiver wakeup by idle-line or address-mark; address match feature in receiver to reduce address-mark wakeup ISR overhead; 1/16 bit-time noise detection; DMA transmission for both transmit and receive
  - SPI — Two serial peripheral interfaces with full-duplex or single-wire bidirectional option; double-buffered transmitter and receiver; master or slave mode operation; selectable MSB-first or LSB-first shifting; 8-bit or 16-bit data modes; programmable transmit bit rate; receive data buffer hardware match feature; DMA transmission for transmit and receive
- Input/Output
  - Up to 69 GPIOs and one Input-only pin
  - Interrupt or DMA request with selectable polarity on all input pins
  - Programmable glitch filter, hysteresis and configurable pull up/down device on all input pins
  - Configurable slew rate and drive strength on all output pins
  - Independent pin value register to read logic level on digital pin
  - Up to 16 rapid general purpose I/O (RGPIO) pins connected to the processor’s local 32-bit platform bus with set, clear, and faster toggle functionality

1 MCF51AG128 Family Configurations

1.1 Device Comparison

The following table compares the various device derivatives available within the MCF51AG128 series MCUs.

Table 1. MCF51AG128 Series Device Comparison

Feature	MCF51AG128			MCF51AG96		
	80-pin	64-pin	48-pin	80-pin	64-pin	48-pin
Flash memory size (KB)	128			96		
RAM size (KB)	16					
ColdFire V1 core with BDM (background debug module)	Yes					
HSCMP (analog comparator)	2	2	1	2	2	1
ADC (analog-to-digital converter) channels (12-bit)	24	19	12	24	19	12
CRC (cyclic redundancy check)	Yes					
DAC	2	2	1	2	2	1
DMA controller	4-ch					
iEvent (intelligent Event module)	Yes					
EWM (External Watchdog Monitor)	Yes					
WDOG (Watchdog timer)	Yes					
RTC	Yes					
DBG (debug module)	Yes					
IIC (inter-integrated circuit)	1	1	No	1	1	No
IRQ (interrupt request input)	Yes					
INTC (interrupt controller)	Yes					
LVD (low-voltage detector)	Yes					
ICS (internal clock source)	Yes					
OSC (crystal oscillator)	Yes					
Port I/O[1]	69	53	39	69	53	39
RGPIO (rapid general-purpose I/O)	16	16	15	16	16	15
SCI (serial communications interface)	2					
SPI1 (serial peripheral interface)	Yes					
SPI2 (serial peripheral interface)	Yes	No	No	Yes	No	No
FTM1 (flexible timer module) channels	6[2]					
FTM2 channels	6[2]					

Figure 3 shows the pinout of the 64-pin LQFP and QFP.

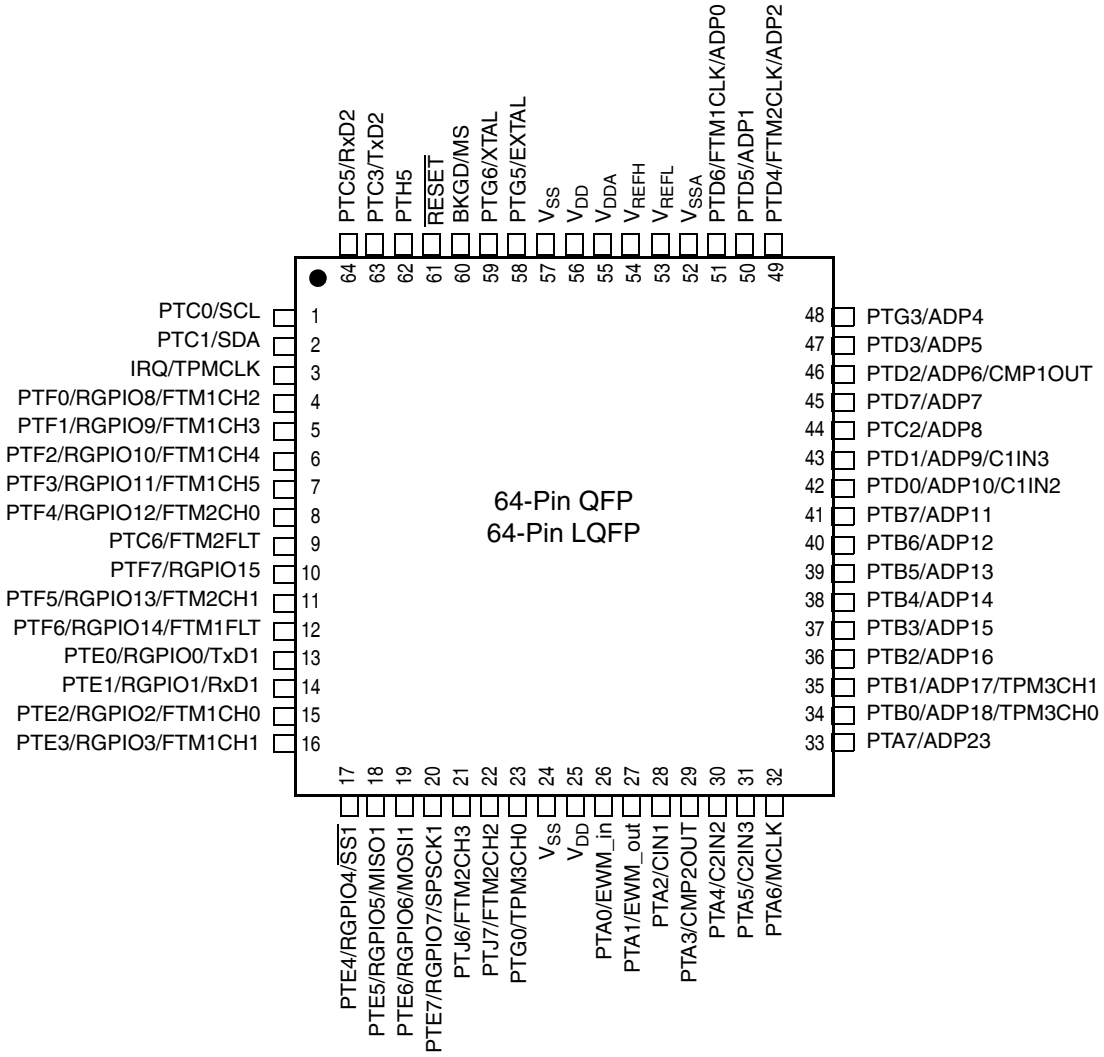


Figure 3. 64-Pin QFP and LQFP

Table 5. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	–0.3 to 5.8	V
Input voltage	V_{In}	–0.3 to V_{DD} + 0.3	V
Instantaneous maximum current Single pin limit (applies to all port pins)[1, 2, 3]	I_D	±25	mA
Maximum current into V_{DD}	I_{DD}	120	mA
Storage temperature	T_{stg}	–55 to 150	°C

1 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

2 All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.

3 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low which would reduce overall power consumption.

2.3 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} is very small.

Table 6. Thermal Characteristics

Rating		Symbol	Value	Unit
Operating temperature range (packaged)		T_A	–40 to 105	°C
Maximum junction temperature		T_J	150	°C
Thermal resistance [1,2,3,4]				
80-pin LQFP				
	1s	θ_{JA}	56	°C/W
	2s2p		45	
64-pin QFP				
	1s		54	
	2s2p		41	
64-pin LQFP				
	1s		67	
	2s2p		49	
48-pin LQFP				
	1s		69	
	2s2p		51	

1 Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

2 Junction to Ambient Natural Convection

3 1s — Single layer board, one signal layer

4 2s2p — Four layer board, 2 signal and 2 power layers

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \quad \textit{Eqn. 1}$$

where:

T_A = Ambient temperature, °C

θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W

$P_D = P_{int} + P_{I/O}$

$P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power

$P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273\ °C) \quad \textit{Eqn. 2}$$

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273°C) + \theta_{JA} \times (P_D)^2 \quad \textit{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from Equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A.

2.4 Electrostatic Discharge (ESD) Protection Characteristics

Although damage from static discharge is much less common on these devices than on early CMOS circuits, normal handling precautions should be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with CDF-AEC-Q00 Stress Test Qualification for Automotive Grade Integrated Circuits. (http://www.aecouncil.com/) This device was qualified to AEC-Q100 Rev E.

A device is considered to have failed if, after exposure to ESD pulses, the device no longer meets the device specification requirements. Complete dc parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 7. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
Human Body	Series Resistance	R1	1500	Ω
	Storage Capacitance	C	100	pF
	Number of Pulse per pin	—	3	—

Table 7. ESD and Latch-up Test Conditions (continued)

Model	Description	Symbol	Value	Unit
Latch-up	Minimum input voltage limit	—	–2.5	V
	Maximum input voltage limit	—	7.5	V

Table 8. ESD and Latch-Up Protection Characteristics

Num	Rating	Symbol	Min	Max	Unit
1	Human Body Model (HBM)	V_{HBM}	±2000	—	V
2	Charge Device Model (CDM)	V_{CDM}	±500	—	V
3	Latch-up Current at T_A = 85°C	I_{LAT}	±100	—	mA

2.5 DC Characteristics

This section includes information about power supply requirements, I/O pin characteristics, and power supply current in various operating modes.

Table 9. DC Characteristics

Num	C	Parameter	Symbol	Min	Typical[1]	Max	Unit
1	—	Operating voltage		2.7	—	5.5	V
2	P	Output high voltage — Low Drive (PTxDSn = 0) 5 V, I_{Load} = –5 mA 3 V, I_{Load} = –1.5 mA 5V, I_{Load} = –3 mA, PTC0 and PTC1 3V, I_{Load} = –1.5 mA, PTC0 and PTC1	V_{OH}	 V_{DD} – 1.5 V_{DD} – 0.8 V_{DD} – 0.4 V_{DD} – 0.4	 — — — —	 — — — —	V
		Output high voltage — High Drive (PTxDSn = 1) 5 V, I_{Load} = –20 mA 3 V, I_{Load} = –8 mA 5V, I_{Load} = –12 mA, PTC0 and PTC1 3V, I_{Load} = –8 mA, PTC0 and PTC1		 V_{DD} – 1.5 V_{DD} – 0.8 V_{DD} – 0.4 V_{DD} – 0.4	 — — — —	 — — — —	
3	P	Output low voltage — Low Drive (PTxDSn = 0) 5 V, I_{Load} = 5 mA 3 V, I_{Load} = 1.5 mA 5V, I_{Load} = 3 mA, PTC0 and PTC1 3V, I_{Load} = 1.5 mA, PTC0 and PTC1	V_{OL}	 — — — —	 — — — —	 1.5 0.8 0.4 0.4	V
		Output low voltage — High Drive (PTxDSn = 1) 5 V, I_{Load} = 20 mA 3 V, I_{Load} = 8 mA 5V, I_{Load} = 12 mA, PTC0 and PTC1 3V, I_{Load} = 8 mA, PTC0 and PTC1		 — — — —	 — — — —	 1.5 0.8 0.4 0.4	
4	C	Output high current — Max total I_{OH} for all ports 5V 3V	I_{OHT}	 — —	 — —	 100 60	mA
5	C	Output low current — Max total I_{OL} for all ports 5 V 3 V	I_{OLT}	 — —	 — —	 100 60	mA

Table 10. Supply Current Characteristics

Num	C	Parameter	Symbol	V_{DD} (V)	Typical[1]	Max[2]	Unit
14		Stop3 mode supply current	$S3I_{DD}$				
	C	–40 °C		5	1.2	3	μA
	P	25 °C			1.7	3	
	C	105 °C			43.3	60	
	C	–40 °C		3	1.04	3	μA
	P	25 °C			1.6	3	
	C	105 °C			45.5	60	
15		Stop4 mode supply current	$S4I_{DD}$				
	C	–40 °C		5	106	130	μA
	P	25 °C			109	130	
	C	105 °C			155	170	
	C	–40 °C		3	95	130	μA
	P	25 °C			98	130	
	C	105 °C			142	170	
16	C	RTC adder to stop2 or stop3[5], 25 °C	$S23I_{DDRTC}$	5	300	—	nA
				3	300	—	nA
17	C	Adder to stop3 for oscillator enabled[6] (ERCLKEN = 1 and EREFSTEN = 1)	$S3I_{DDOSC}$	5, 3	5	—	μA

1 Typicals are measured at 25 °C.

2 Values given here are preliminary estimates prior to completing characterization.

3 Code run from flash, FEI mode, and does not include any dc loads on port pins. Bus CLK= (CPU CLK/2)

4 GPIO filters are working on LPO clock.

5 Most customers are expected to use auto-wakeup from stop2 or stop3 instead of the higher current wait mode.

6 Values given under the following conditions: low range operation (RANGE = 0), low power mode (HGO = 0).

Figure 9. Run Current at Different Conditions

Table 13. 5 V 12-bit ADC Characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) (continued)

Num	C	Characteristic	Conditions	Symb	Min	Typical[1]	Max	Unit	Comment
16	D	Temp Sensor Voltage	25 °C	V_{TEMP25}	—	1.396	—	mV	—
17	D	Temp Sensor Slope	–40 °C — 25 °C	m	—	3.266	—	mV/°C	—
			25 °C — 85 °C		—	3.638	—		

1 Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

2 1 LSB = $(V_{REFH} - V_{REFL})/2^N$

3 Monotonicity and No-Missing-Codes guaranteed in 10 bit and 8 bit modes

4 Based on input pad leakage current. Refer to pad electricals.

2.10 External Oscillator (XOSC) Characteristics

Table 14. Oscillator Electrical Specifications (Temperature Range = –40 to 105 °C Ambient)

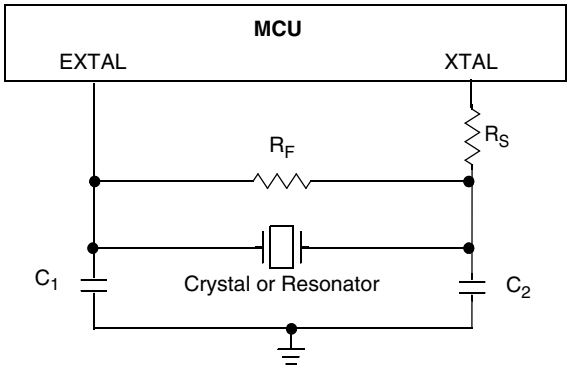
Num	C	Rating	Symbol	Min	Typical[1]	Max	Unit
1	C	Oscillator crystal or resonator (EREFS = 1, ERCLKEN = 1) Low range (RANGE = 0) High range (RANGE = 1) FEE or FBE mode [2] High range (RANGE = 1, HGO = 1) FBELP mode High range (RANGE = 1, HGO = 0) FBELP mode	 f_{lo} f_{hi} f_{hi-hgo} f_{hi-lp}	 32 1 1 1	 — — — —	 38.4 16 16 8	 kHz MHz MHz MHz
2	—	Load capacitors	C_1 C_2	See crystal or resonator manufacturer's recommendation.			
3	—	Feedback resistor Low range (32 kHz to 100 kHz) High range (1 MHz to 16 MHz)	R_F		10 1	—	MΩ
4	—	Series resistor Low range, low gain (RANGE = 0, HGO = 0) Low range, high gain (RANGE = 0, HGO = 1) High range, low gain (RANGE = 1, HGO = 0) High range, high gain (RANGE = 1, HGO = 1) ≥ 8 MHz 4 MHz 1 MHz	R_S	 — — — — — —	 0 100 0 0 0 0	 — — — 0 10 20	kΩ
5	T	Crystal start-up time [3] Low range, low gain (RANGE = 0, HGO = 0) Low range, high gain (RANGE = 0, HGO = 1) High range, low gain (RANGE = 1, HGO = 0)[4] High range, high gain (RANGE = 1, HGO = 1)[3]	 $t_{CSTL-LP}$ $t_{CSTL-HGO}$ $t_{CSTH-LP}$ $t_{CSTH-HGO}$	 — — — —	 1500 2000 3 7	 — — — —	ms
6	T	Square wave input clock frequency (EREFS = 0, ERCLKEN = 1) FEE mode [2] FBE mode[2] FBELP mode	f_{extal}	 0.03125 0 0	 — — —	 50.33 50.33 50.33	MHz

1 Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.

2 When MCG is configured for FEE or FBE mode, input clock source must be divisible using RDIV to within the range of 31.25 kHz to 39.0625 kHz.

3 This parameter is characterized and not tested on each device. Proper PC board layout procedures must be followed to achieve specifications.

4 4 MHz crystal



2.11 ICS Specifications

Table 15. ICS Frequency Specifications (Temperature Range = –40 to 105 °C Ambient)

Num	C	Rating		Symbol	Min	Typical[1]	Max	Unit
1	C	Internal reference frequency - factory trimmed at V_{DD} = 5 V and temperature = 25 °C		f_{int_ft}	—	32.768	—	kHz
2	C	Average internal reference frequency – untrimmed		f_{int_ut}	31.25	—	39.06	kHz
3	T	Internal reference startup time		t_{irefst}	—	60	100	µs
4	C	DCO output frequency range - untrimmed [2]	Low range (DRS = 00)	f_{dco_ut}	16	—	20	MHz
	C		Mid range (DRS = 01)		32	—	40	
	C		High range (DRS = 10)		48	—	60	
5	P	DCO output frequency[2] Reference =32768Hz and DMX32 = 1	Low range (DRS = 00)	f_{dco_DMX32}	—	16.82	—	MHz
	P		Mid range (DRS = 01)		—	33.69	—	
	P		High range (DRS = 10)		—	50.48	—	
6	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (using FTRIM)		$\Delta f_{dco\_res\_t}$	—	±0.1	±0.2	$\%f_{dco}$
7	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (not using FTRIM)		$\Delta f_{dco\_res\_t}$	—	±0.2	±0.4	$\%f_{dco}$
8	D	Total deviation of trimmed DCO output frequency over full voltage and temperature range		Δf_{dco_t}	—	0.5 –1.0	±2	$\%f_{dco}$
9	D	Total deviation of trimmed DCO output frequency over fixed voltage and temperature range of 0 –70 °C		Δf_{dco_t}	—	±0.5	±1	$\%f_{dco}$

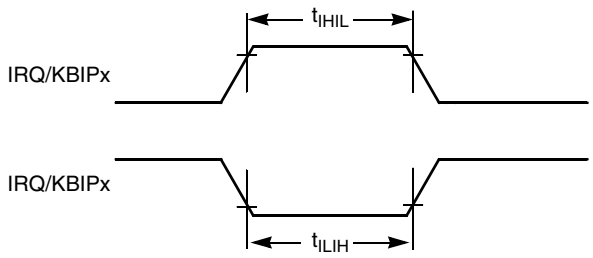


Figure 12. IRQ/KBIPx Timing

2.12.2 Timer (TPM/FTM) Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 17. TPM/FTM Input Timing

NUM	C	Function	Symbol	Min	Max	Unit
1	—	External clock frequency	f_{TPMext}	DC	$f_{Bus}/4$	MHz
2	—	External clock period	t_{TPMext}	4	—	t_{cyc}
3	D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
4	D	External clock low time	t_{clkl}	1.5	—	t_{cyc}
5	D	Input capture pulse width	t_{ICPW}	1.5	—	t_{cyc}

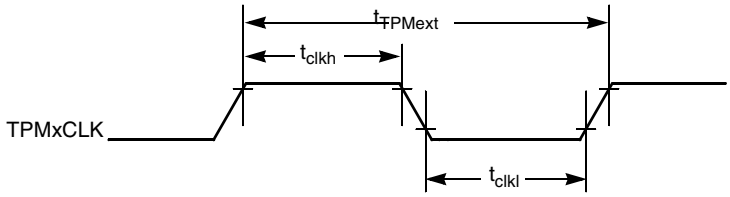


Figure 13. Timer External Clock

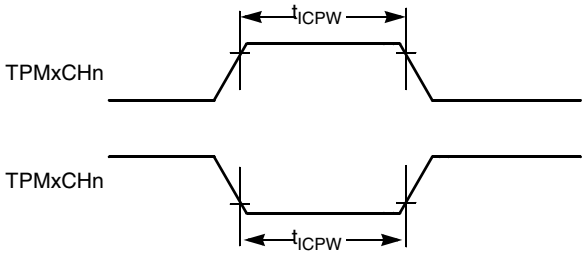
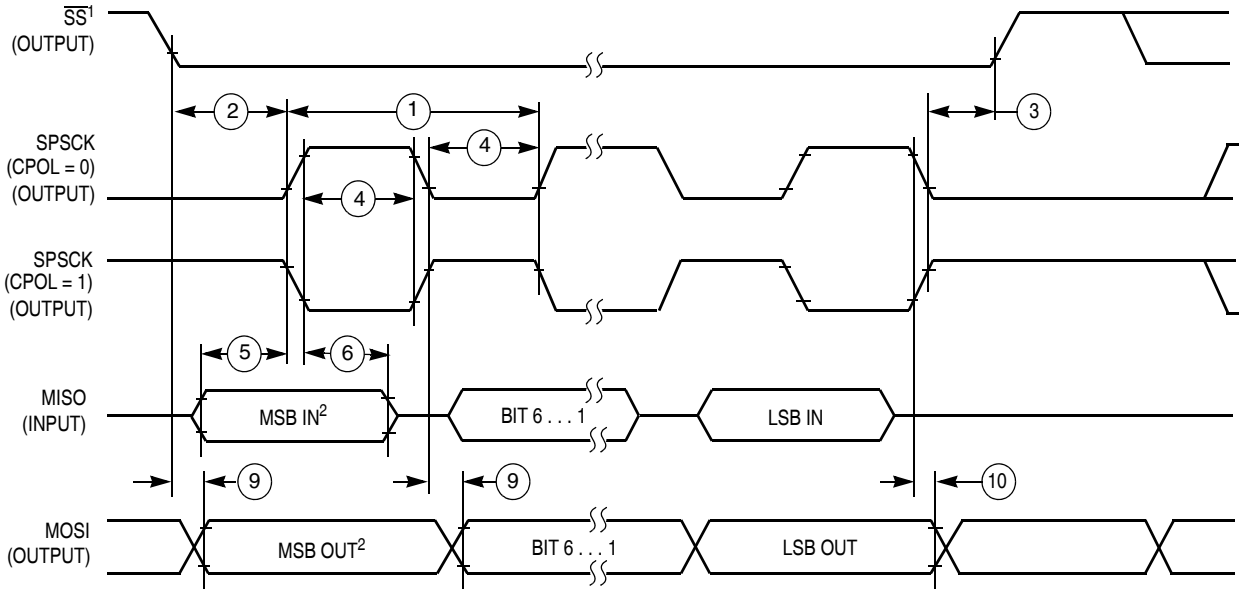


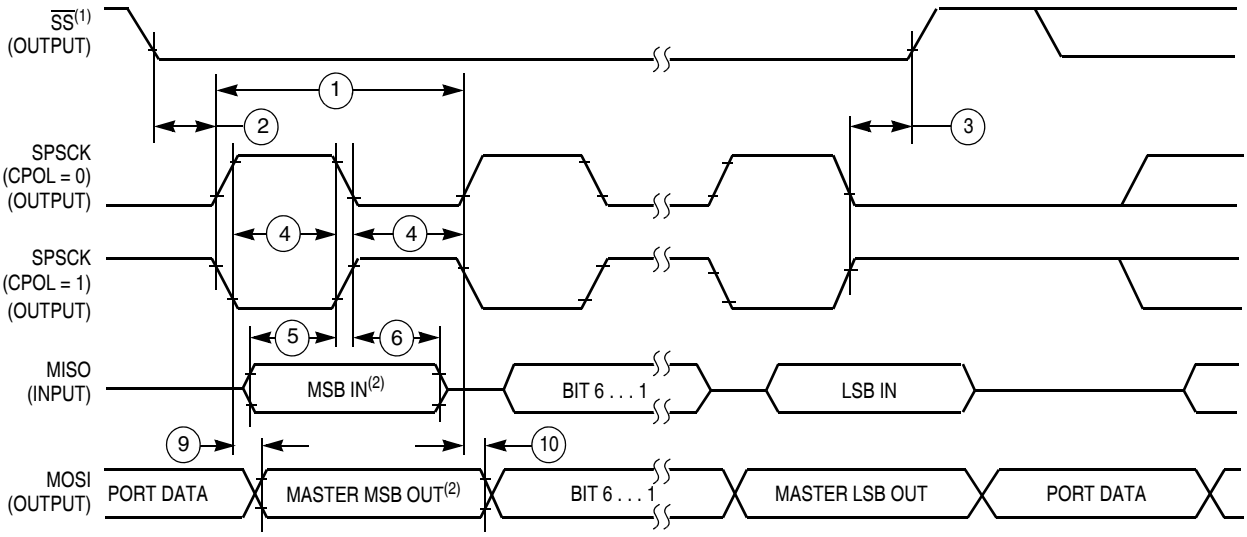
Figure 14. Timer Input Capture Pulse



NOTES:

1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

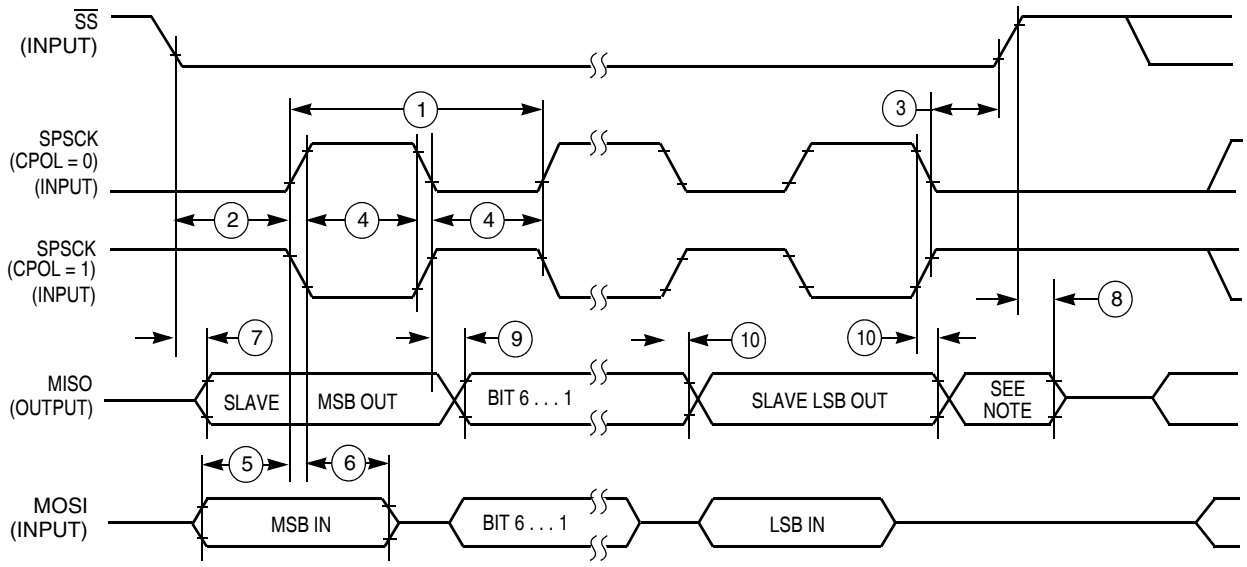
Figure 15. SPI Master Timing (CPHA = 0)



NOTES:

1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

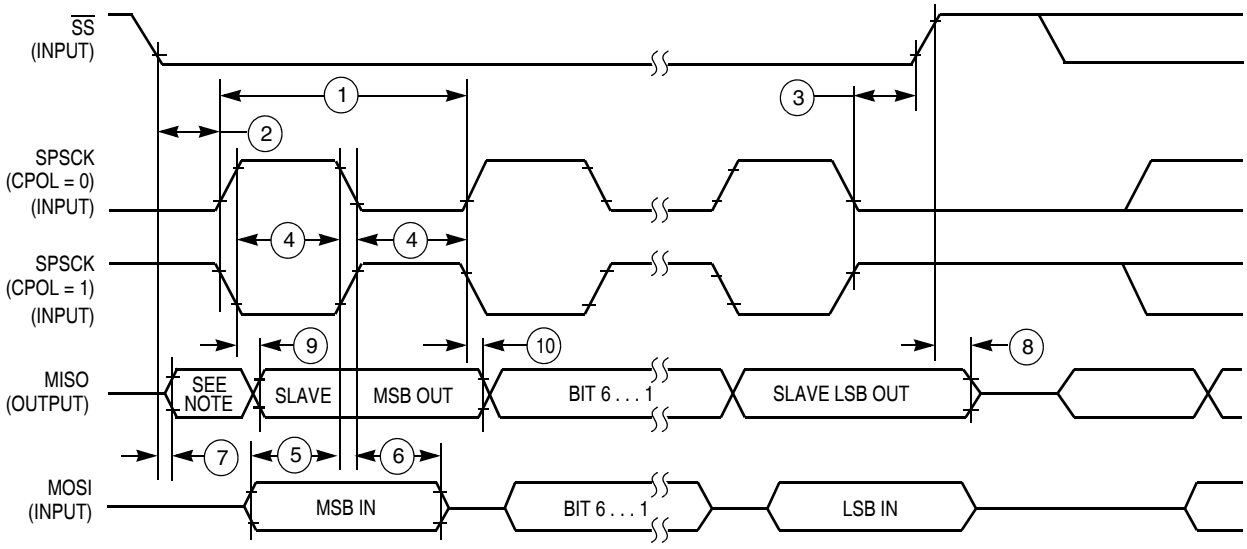
Figure 16. SPI Master Timing (CPHA = 1)



NOTE:

1. Not defined but normally MSB of character just received

Figure 17. SPI Slave Timing (CPHA = 0)



NOTE:

1. Not defined but normally LSB of character just received

Figure 18. SPI Slave Timing (CPHA = 1)

2.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the Flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see *MCF51AG128 Reference Manual*.

Table 19. Flash Characteristics

Num	C	Characteristic	Symbol	Min	Typical[1]	Max	Unit
1	—	Supply voltage for program/erase	$V_{prog/erase}$	2.7		5.5	V
2	—	Supply voltage for read operation	V_{Read}	2.7		5.5	V
3	—	Internal FCLK frequency[2]	f_{FCLK}	150		200	kHz
4	—	Internal FCLK period (1/FCLK)	t_{Fcyc}	5		6.67	µs
5	—	Byte program time (random location)[2]	t_{prog}	9			t_{Fcyc}
6	—	Byte program time (burst mode)[2]	t_{Burst}	4			t_{Fcyc}
7	—	Page erase time[3]	t_{Page}	4000			t_{Fcyc}
8	—	Mass erase time[2]	t_{Mass}	20,000			t_{Fcyc}
9	C	Program/erase endurance[4] T_L to T_H = –40 °C to 105 °C T = 25 °C		10,000 —	— 100,000	— —	cycles
10	C	Data retention[5]	t_{D_ret}	15	100	—	years

1 Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

2 The frequency of this clock is controlled by a software setting.

3 These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

4 **Typical endurance for flash** was evaluated for this product family on the HC9S12Dx64. For additional information on how Freescale Semiconductor defines typical endurance, please refer to Engineering Bulletin EB619/D, *Typical Endurance for Nonvolatile Memory*.

5 **Typical data retention** values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25 °C using the Arrhenius equation. For additional information on how Freescale Semiconductor defines typical data retention, please refer to Engineering Bulletin EB618/D, *Typical Data Retention for Nonvolatile Memory.*

2.14 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

2.14.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM Cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (North and East). For more detailed information concerning the evaluation results, conditions and setup, please refer to the EMC Evaluation Report for this device.

3 Ordering Information

This section contains ordering information for MCF51AG128 devices.

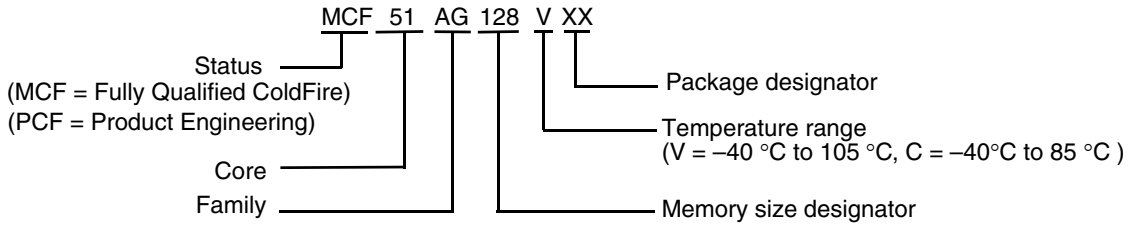


Table 20. Orderable Part Number Summary

Freescale Part Number	Description	Flash / SRAM (KB)	Package	Temperature
MCF51AG128VLK	MCF51AG128 ColdFire Microcontroller	128 / 16	80 LQFP	–40°C to 105°C
MCF51AG128VLH	MCF51AG128 ColdFire Microcontroller	128 / 16	64 LQFP	–40°C to 105°C
MCF51AG128VQH	MCF51AG128 ColdFire Microcontroller	128 / 16	64 QFP	–40°C to 105°C
MCF51AG128VLF	MCF51AG128 ColdFire Microcontroller	128 / 16	48 LQFP	–40°C to 105°C
MCF51AG96VLK	MCF51AG96 ColdFire Microcontroller	96 / 16	80 LQFP	–40°C to 105°C
MCF51AG96VLH	MCF51AG96 ColdFire Microcontroller	96 / 16	64 LQFP	–40°C to 105°C
MCF51AG96VQH	MCF51AG96 ColdFire Microcontroller	96 / 16	64 QFP	–40°C to 105°C
MCF51AG96VLF	MCF51AG96 ColdFire Microcontroller	96 / 16	48 LQFP	–40°C to 105°C

4 Package Information

Table 21. Package Descriptions

Pin Count	Package Type	Abbreviation	Designator	Case No.	Document No.
80	Low Quad Flat Package	LQFP	LK	917A	98ASS23237W
64	Low Quad Flat Package	LQFP	LH	840F	98ASS23234W
64	Quad Flat Package	QFP	QH	840B	98ASB42844B
48	Low Quad Flat Package	LQFP	LF	932	98ASH00962A

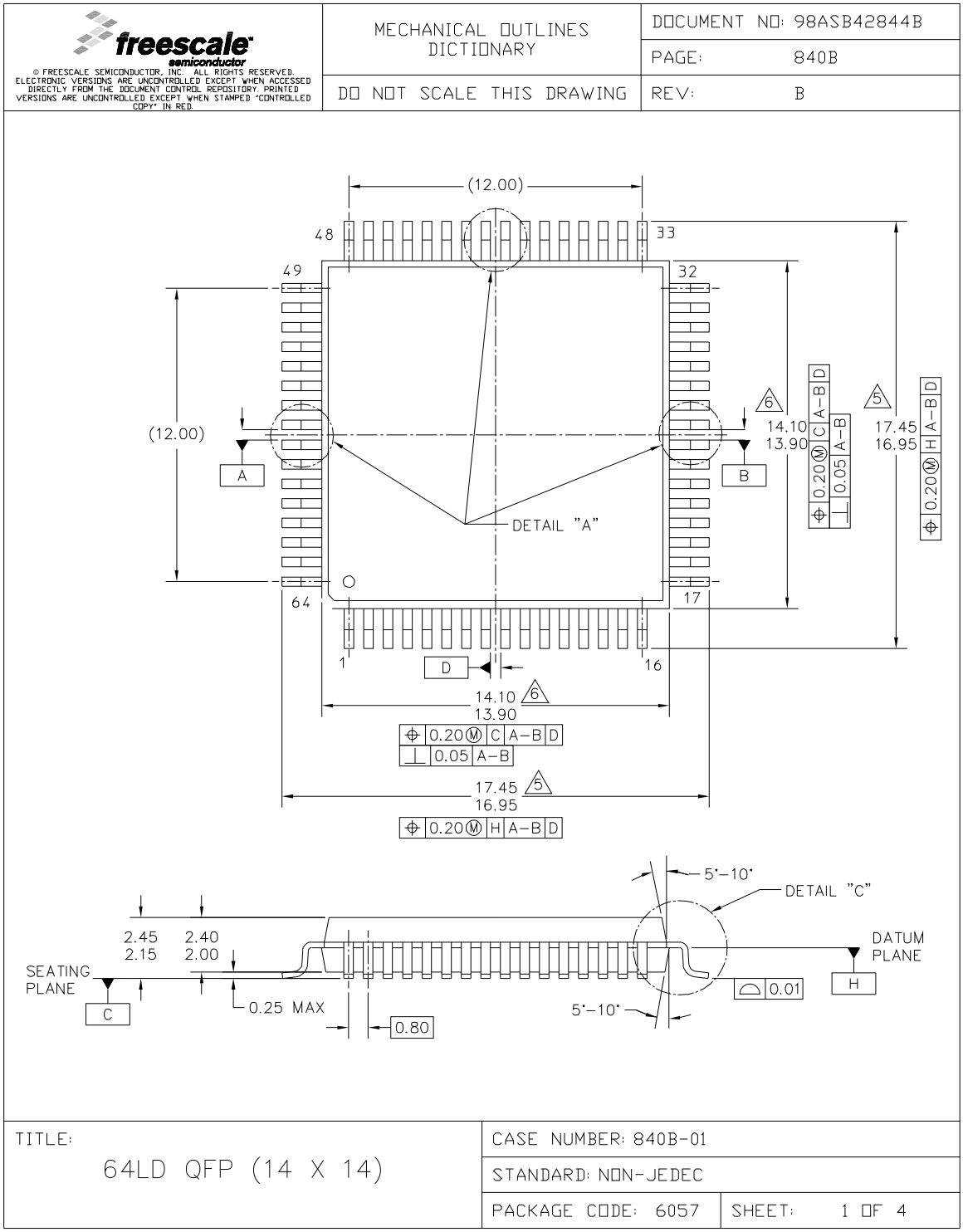
freescale semiconductor	MECHANICAL OUTLINES DICTIONARY	DOCUMENT NO: 98ASS23234W
		PAGE: 840F
	DO NOT SCALE THIS DRAWING	REV: E

NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994.
3. DATUMS A, B AND D TO BE DETERMINED AT DATUM PLANE H.
4. DIMENSIONS TO BE DETERMINED AT SEATING PLANE C.
5. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE UPPER LIMIT BY MORE THAN 0.08 mm AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD SHALL NOT BE LESS THAN 0.07 mm.
6. THIS DIMENSION DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. THIS DIMENSION IS MAXIMUM PLASTIC BODY SIZE DIMENSION INCLUDING MOLD MISMATCH.
7. EXACT SHAPE OF EACH CORNER IS OPTIONAL.
8. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.1 mm AND 0.25 mm FROM THE LEAD TIP.

TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	CASE NUMBER: 840F–02	
	STANDARD: JEDEC MS–026 BCD	
	PACKAGE CODE: 8426	SHEET: 3

5.3 64-pin QFP Package



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		PAGE: 840B
	DO NOT SCALE THIS DRAWING	REV: B

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DATUM PLANE −H− IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.
4. DATUMS A−B AND −D− TO BE DETERMINED AT DATUM PLANE −H−.
5. DIMENSIONS TO BE DETERMINED AT SEATING PLANE −C−.
6. DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25mm PER SIDE. DIMENSIONS DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE −H−.
7. DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08mm TOTAL IN EXCESS OF THE DIMENSION AT MAXIMUM MATERIAL CONDICTION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT.

TITLE: 64LD QFP (14 X 14)	CASE NUMBER: 840B−01	
	STANDARD: NON−JEDEC	
	PACKAGE CODE: 6057	SHEET: 3 OF 4

5.4 48-pin LQFP Package

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